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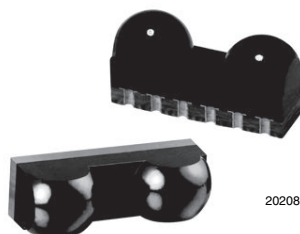




**TFBS4711**

Vishay Semiconductors

## Serial Infrared Transceiver SIR, 115.2 kbit/s, 2.4 V to 5.5 V Operation



**RoHS**  
COMPLIANT

### DESCRIPTION

The TFBS4711 is a low profile, infrared data transceiver module. It supports IrDA® data rates up to 115.2 kbit/s (SIR). The transceiver module consists of a PIN photodiode, an infrared emitter (IRED), and a low-power CMOS control IC to provide a total front-end solution in a single package.

The device is designed for the low power IrDA standard with an extended range on-axis up to 1 m. The RXD output pulse width is independent of the optical input pulse width and stays always at a fixed pulse width thus making the device optimum for standard endecds. TFBS4711 has a tri-state output and is floating in shut-down mode with a weak pull-up. The shut down (SD) feature cuts current consumption to typically 10 nA.

### APPLICATIONS

- Ideal for battery operated devices
- PDAs
- Mobile phones
- Electronic wallet (IrFM)
- Notebook computers
- Digital still and video cameras
- Printers, fax machines, photocopiers, screen projectors
- Data loggers
- External infrared adapters (dongles)
- Diagnostics systems
- Medical and industrial data collection devices
- Kiosks, POS, point and pay devices
- GPS
- Access control
- Field programming devices

### FEATURES

- Compliant with the latest IrDA physical layer low power specification (9.6 kbit/s to 115.2 kbit/s)
- Small package (H x L x W in mm): 1.9 x 3 x 6
- Typical link distance on-axis up to 1 m
- Battery and power management features:
  - > Idle current - 70  $\mu$ A typical
  - > Shutdown current - 10 nA typical
  - > Operates from 2.4 V to 5.5 V within specification over full temperature range from - 25 °C to + 85 °C
- Remote control - transmit distance up to 8 m
- Tri-state receiver output, floating in shutdown with a weak pull-up
- Constant RXD output pulse width (2.2  $\mu$ s typical)
- Meets IrFM fast connection requirements
- Split power supply, an independent, unregulated supply for IRED anode and a well regulated supply for V<sub>CC</sub>
- Directly interfaces with various super I/O and controller devices and encoder/decoder such as TOIM4232 or TOIM5232
- Qualified for lead (Pb)-free and Sn/Pb processing (MSL4)
- Compliant to RoHS directive 2002/95/EC and in accordance to WEEE 2002/96/EC

### PARTS TABLE

| PART NUMBER  | DESCRIPTION   | QTY/REEL |
|--------------|---|----------|
| TFBS4711-TR1 | Oriented in carrier tape for side view surface mounting | 1000 pcs |
| TFBS4711-TR3 | Oriented in carrier tape for side view surface mounting | 2500 pcs |
| TFBS4711-TT1 | Oriented in carrier tape for top view surface mounting  | 1000 pcs |



## TFBS4711

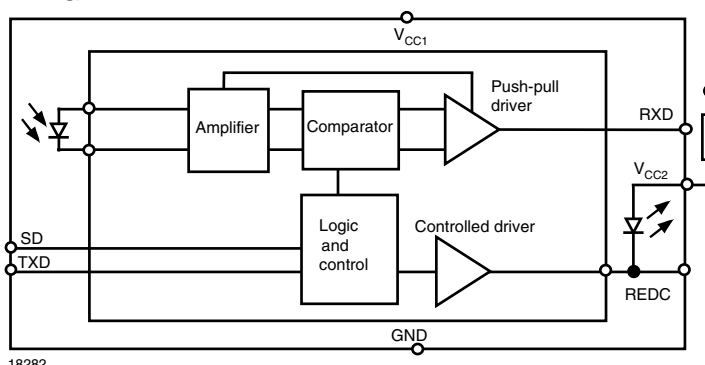
Vishay Semiconductors Serial Infrared Transceiver SIR, 115.2 kbit/s,  
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### PRODUCT SUMMARY

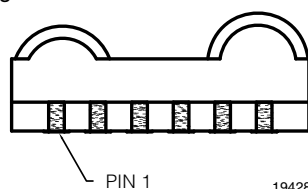
| PART NUMBER | DATA RATE (kbit/s) | DIMENSIONS H x L x W (mm) | LINK DISTANCE (m) | OPERATING VOLTAGE (V) | IDLE SUPPLY CURRENT (mA) |
|-------------|--------------------|---------------------------|-------------------|-----------------------|--------------------------|
| TFBS4711    | 115.2              | 1.9 x 3 x 6               | 0 to ≥ 0.7        | 2.4 to 5.5            | 0.07                     |

### FUNCTIONAL BLOCK DIAGRAM



### PINOUT

TFBS4711  
weight 50 mg



### Definitions:

In the Vishay transceiver datasheets the following nomenclature is used for defining the IrDA operating modes:  
SIR: 2.4 kbit/s to 115.2 kbit/s, equivalent to the basic serial infrared standard with the physical layer version IrPhy 1.0  
MIR: 576 kbit/s to 1152 kbit/s  
FIR: 4 Mbit/s  
VFIR: 16 Mbit/s  
MIR and FIR were implemented with IrPhy 1.1, followed by IrPhy 1.2, adding the SIR low power standard.

### PIN DESCRIPTION

| PIN NUMBER | SYMBOL                            | DESCRIPTION   | I/O | ACTIVE |
|------------|-----------------------------------|---|-----|--------|
| 1          | V <sub>CC2</sub><br>IRED<br>anode | Connect IRED anode directly to the power supply (V <sub>CC2</sub> ). IRED current can be decreased by adding a resistor in series between the power supply and IRED anode. A separate unregulated power supply can be used at this pin  |     |        |
| 2          | TXD                               | This Schmitt-Trigger input is used to transmit serial data when SD is low. An on-chip protection circuit disables the LED driver if the TXD pin is asserted for longer than 100 μs. The input threshold voltage adapts to and follows the logic voltage swing defined by the applied supply voltage   | I   | High   |
| 3          | RXD                               | Received data output, push-pull CMOS driver output capable of driving standard CMOS or TTL loads. During transmission the RXD output is active and mirrors the transmit signal. No external pull-up or pull-down resistor is required. Floating with a weak pull-up of 500 kΩ (typ.) in shutdown mode. The voltage swing is defined by the applied supply voltage | O   | Low    |
| 4          | SD                                | Shutdown. The input threshold voltage adapts to and follows the logic voltage swing defined by the applied supply voltage   | I   | High   |
| 5          | V <sub>CC1</sub>                  | Supply voltage  |     |        |
| 6          | GND                               | Ground  |     |        |





## TFBS4711

Serial Infrared Transceiver SIR, 115.2 kbit/s, Vishay Semiconductors  
 2.4 V to 5.5 V Operation

### ABSOLUTE MAXIMUM RATINGS <sup>(1)</sup>

| PARAMETER  | TEST CONDITIONS                                     | SYMBOL                 | MIN.  | TYP. | MAX.                   | UNIT |
|--|---|------------------------|-------|------|------------------------|------|
| Supply voltage range, transceiver                  | - 0.3 V < V <sub>CC2</sub> < 6 V                    | V <sub>CC1</sub>       | - 0.5 |      | + 6                    | V    |
| Supply voltage range, transmitter                  | - 0.5 V < V <sub>CC1</sub> < 6 V                    | V <sub>CC2</sub>       | - 0.5 |      | + 6                    | V    |
| RXD output voltage                                 | - 0.5 V < V <sub>CC1</sub> < 6 V                    | V <sub>RXD</sub>       | - 0.5 |      | V <sub>CC1</sub> + 0.5 | V    |
| Voltage at all inputs                              | Note: V <sub>in</sub> ≥ V <sub>CC1</sub> is allowed | V <sub>in</sub>        | - 0.5 |      | + 6                    | V    |
| Input current                                      | For all pins except IRED anode pin                  | I <sub>CC</sub>        |       |      | 10                     | mA   |
| Output sink current                                |   |                        |       |      | 25                     | mA   |
| Power dissipation                                  | See derating curve                                  | P <sub>D</sub>         |       |      | 250                    | mW   |
| Junction temperature                               |   | T <sub>j</sub>         |       |      | 125                    | °C   |
| Ambient temperature range (operating)              |   | T <sub>amb</sub>       | - 25  |      | + 85                   | °C   |
| Storage temperature range                          |   | T <sub>stg</sub>       | - 40  |      | + 100                  | °C   |
| Soldering temperature                              | See recommended solder profile                      |                        |       |      | 260                    | °C   |
| Average output current, pin 1                      |   | I <sub>IRED</sub> (DC) |       |      | 85                     | mA   |
| Repetitive pulsed output current<br>pin 1 to pin 2 | t < 90 μs, t <sub>on</sub> < 20 %                   | I <sub>IRED</sub> (RP) |       |      | 430                    | mA   |
| ESD protection                                     |   | V <sub>ESD</sub>       | 1     |      |                        | kV   |
| Latchup  |   |                        | ± 100 |      |                        | mA   |

#### Note

<sup>(1)</sup> Reference point ground, pin 6 unless otherwise noted.

Typical values are for design aid only, not guaranteed nor subject to production testing.

We apologize to use sometimes in our documentation the abbreviation LED and the word light emitting diode instead of infrared emitting diode (IRED) for IR-emitters. That is by definition wrong; we are here following just a bad trend.

### EYE SAFETY INFORMATION

| STANDARD  | CLASSIFICATION |
|---|----------------|
| IEC/EN 60825-1 (2007-03), DIN EN 60825-1 (2008-05) "SAFETY OF LASER PRODUCTS - Part 1: equipment classification and requirements", simplified method  | Class 1        |
| IEC 62471 (2006), CIE S009 (2002) "Photobiological Safety of Lamps and Lamp Systems"  | Exempt         |
| DIRECTIVE 2006/25/EC OF THE EUROPEAN PARLIAMENT AND OF THE COUNCIL of 5 <sup>th</sup> April 2006 on the minimum health and safety requirements regarding the exposure of workers to risks arising from physical agents (artificial optical radiation) (19 <sup>th</sup> individual directive within the meaning of article 16(1) of directive 89/391/EEC) | Exempt         |

#### Note

Vishay transceivers operating inside the absolute maximum ratings are classified as eye safe according the above table.



## TFBS4711

Vishay Semiconductors Serial Infrared Transceiver SIR, 115.2 kbit/s,  
2.4 V to 5.5 V Operation



| ELECTRICAL CHARACTERISTICS <sup>(1)</sup>                     |  |           |                      |                      |           |        |
|---|--|-----------|----------------------|----------------------|-----------|--------|
| PARAMETER   | TEST CONDITIONS  | SYMBOL    | MIN.                 | TYP.                 | MAX.      | UNIT   |
| TRANSCEIVER   |  |           |                      |                      |           |        |
| Supply voltage  |  | $V_{CC1}$ | 2.4                  |                      | 5.5       | V      |
| Operating temperature range                                   |  | $T_A$     | - 25                 |                      | + 85      | °C     |
| Data rates  |  |           | 9.6                  |                      | 115.2     | kbit/s |
| Idle supply current at $V_{CC1}$<br>(receive mode, no signal) | SD = low,<br>$T_{amb} = - 25\text{ °C to } + 85\text{ °C}$<br>independent of ambient light,<br>$V_{CC1} = V_{CC2} = 2.4\text{ V to } 5.5\text{ V}$ | $I_{CC1}$ | 40                   | 70                   | 150       | μA     |
|   | SD = low, $T_{amb} = 25\text{ °C}$ ,<br>$V_{CC1} = V_{CC2} = 2.4\text{ V to } 5.5\text{ V}$  | $I_{CC1}$ | 40                   | 70                   | 100       | μA     |
| Average dynamic supply<br>current, transmitting               | $I_{RED} = 300\text{ mA}$ , 20 % duty cycle  | $I_{CC1}$ |                      | 0.6                  | 2         | mA     |
| Standby (SD) <sup>(2)</sup> supply current                    | SD = high,<br>$T_{amb} = - 25\text{ °C to } + 85\text{ °C}$ ,<br>independent of ambient light  | $I_{SD}$  |                      | 0.01                 | 1         | μA     |
| RXD to $V_{CC1}$ impedance                                    |  | $R_{RXD}$ | 400                  | 500                  | 600       | kΩ     |
| Input voltage low (TXD, SD)                                   |  | $V_{ILO}$ | - 0.3                |                      | 0.4       | V      |
| Input voltage high (SD)                                       | For compliance with $I_{SD}$ spec.   | $V_{IHI}$ | $V_{CC1} - 0.3$      |                      | 6         | V      |
| Input voltage high (TXD)                                      |  | $V_{IHI}$ | $V_{CC1} - 0.5$      |                      | 6         | V      |
| Timing logic decision level                                   |  |           |                      | $0.5 \times V_{CC1}$ |           |        |
| Input leakage current low                                     | $V_{ILO} \leq 0.3\text{ V}$  | $I_{ILO}$ |                      | 0.01                 | 10        | μA     |
| Input leakage current high                                    | $V_{IHI} \geq V_{CC1} - 0.3\text{ V}$  | $I_{IHI}$ |                      | 0.01                 | 10        | μA     |
| Input capacitance (TXD, SD)                                   |  | $C_{IN}$  |                      |                      | 5         | pF     |
| Output voltage low, RXD                                       | $C_{load} = 8\text{ pF}$ , $I_{OLO} \leq   + 500\text{ μA} $   | $V_{OLO}$ |                      |                      | 0.4       | V      |
| Output voltage high, RXD                                      | $I_{OH} = - 200\text{ μA}$   | $V_{OHI}$ | $0.8 \times V_{CC1}$ |                      | $V_{CC1}$ | V      |

### Notes

- (1) Tested at  $T_{amb} = 25\text{ °C}$ ,  $V_{CC1} = V_{CC2} = 2.4\text{ V to } 5.5\text{ V}$  unless otherwise noted.  
 Typical values are for design aid only, not guaranteed nor subject to production testing.  
 (2) SD mode becomes active when SD is set high for more than 0.2 μs. In SD mode the detector is disabled and the output disconnected.

| OPTOELECTRONIC CHARACTERISTICS <sup>(1)</sup>               |  |              |            |             |           |  |
|---|--|--------------|------------|-------------|-----------|--|
| PARAMETER   | TEST CONDITIONS  | SYMBOL       | MIN.       | TYP.        | MAX.      | UNIT                                       |
| RECEIVER  |  |              |            |             |           |  |
| Minimum irradiance $E_e$ in<br>angular range <sup>(3)</sup> | 9.6 kbit/s to 115.2 kbit/s<br>$\lambda = 850\text{ nm to } 900\text{ nm}$ ,<br>$\alpha = 0^\circ, 15^\circ$  | $E_e$        |            | 35<br>(3.5) | 80<br>(8) | mW/m <sup>2</sup><br>(μW/cm <sup>2</sup> ) |
| Maximum irradiance $E_e$ in<br>angular range <sup>(4)</sup> | $\lambda = 850\text{ nm to } 900\text{ nm}$  | $E_e$        |            | 5<br>(500)  |           | kW/m <sup>2</sup><br>(mW/cm <sup>2</sup> ) |
| Maximum no detection<br>irradiance <sup>(2)</sup>           | $\lambda = 850\text{ nm to } 900\text{ nm}$ ,<br>$t_r, t_f < 40\text{ ns}$ ,<br>$t_{po} = 1.6\text{ μs}$ at $f = 115\text{ kHz}$ ,<br>no output signal allowed | $E_e$        | 4<br>(0.4) |             |           | mW/m <sup>2</sup><br>(μW/cm <sup>2</sup> ) |
| Rise time of output signal                                  | 10 % to 90 %, $C_L = 8\text{ pF}$  | $t_{r(RXD)}$ | 10         | 30          | 80        | ns   |
| Fall time of output signal                                  | 90 % to 10 %, $C_L = 8\text{ pF}$  | $t_{f(RXD)}$ | 10         | 30          | 80        | ns   |
| RXD pulse width of output signal                            | Input pulse length > 1.2 μs  | $t_{PW}$     | 1.7        | 2.2         | 3         | μs   |
| Stochastic jitter, leading edge                             | Input irradiance = 100 mW/m <sup>2</sup> ,<br>≤ 115.2 kbit/s   |              |            |             | 350       | ns   |
| Standby/shutdown delay,<br>receiver startup time            | After shutdown active<br>or power-on   |              |            |             | 500       | μs   |
| Latency   |  | $t_L$        |            | 50          | 150       | μs   |





## TFBS4711

Serial Infrared Transceiver SIR, 115.2 kbit/s, Vishay Semiconductors  
2.4 V to 5.5 V Operation

| OPTOELECTRONIC CHARACTERISTICS <sup>(1)</sup>     |   |                 |                  |          |                  |         |
|---|---|-----------------|------------------|----------|------------------|---------|
| PARAMETER   | TEST CONDITIONS   | SYMBOL          | MIN.             | TYP.     | MAX.             | UNIT    |
| <b>TRANSMITTER</b>                                |   |                 |                  |          |                  |         |
| IREC operating current limitation                 | No external resistor for current limitation <sup>(5)</sup>  | $I_D$           | 200              | 300      | 430              | mA      |
| Forward voltage of built-in IRED                  | $I_F = 300$ mA  | $V_f$           | 1.4              | 1.8      | 1.9              | V       |
| Output leakage IRED current                       | $T_{XD} = 0$ V, $0 < V_{CC1} < 5.5$ V   | $I_{IRED}$      | - 1              | 0.01     | 1                | $\mu$ A |
| Output radiant intensity                          | $V_{CC1} = 2.7$ V, $\alpha = 0^\circ, 15^\circ$<br>$T_{XD} = \text{high}$ , SD = low  | $I_e$           | 25               | 65       | 370              | mW/sr   |
|   | $V_{CC1} = 5$ V, $\alpha = 0^\circ, 15^\circ$<br>$T_{XD} = \text{low}$ or SD = high (receiver is inactive as long as SD = high) | $I_e$           |                  |          | 0.04             | mW/sr   |
| Output radiant intensity, angle of half intensity |   | $\alpha$        |                  | $\pm 24$ |                  | deg     |
| Peak-emission wavelength <sup>(6)</sup>           |   | $\lambda_p$     | 880              |          | 900              | nm      |
| Spectral bandwidth                                |   | $\Delta\lambda$ |                  | 45       |                  | nm      |
| Optical rise time                                 |   | $t_{ropt}$      | 10               | 50       | 300              | ns      |
| Optical fall time                                 |   | $t_{fopt}$      | 10               | 50       | 300              | ns      |
| Optical output pulse duration                     | Input pulse width $1.6 < t_{TXD} < 23$ $\mu$ s  | $t_{opt}$       | $t_{TXD} - 0.15$ |          | $t_{TXD} + 0.15$ | $\mu$ s |
|   | Input pulse width $t_{TXD} \geq 23$ $\mu$ s   | $t_{opt}$       | 23               | 50       | 100              | $\mu$ s |
| Optical overshoot                                 |   |                 |                  |          | 25               | %       |

### Notes

- $T_{amb} = 25^\circ\text{C}$ ,  $V_{CC} = 2.4$  V to 5.5 V unless otherwise noted.  
Typical values are for design aid only, not guaranteed nor subject to production testing.
- Equivalent to IrDA background light and electromagnetic field test: fluorescent lighting immunity.
- IrDA sensitivity definition: minimum irradiance  $E_e$  in angular range, power per unit area. The receiver must meet the BER specification while the source is operating at the minimum intensity in angular range into the minimum half-angular range at the maximum link length.
- Maximum irradiance  $E_e$  in angular range, power per unit area. The optical delivered to the detector by a source operating at the maximum intensity in angular range at minimum link length must not cause receiver overdrive distortion and possible related link errors. If placed at the active output interface reference plane of the transmitter, the receiver must meet its bit error ratio (BER). For more definitions see the document "Symbols and Terminology" on the Vishay website.
- Using an external current limiting resistor is allowed and recommended to reduce IRED intensity and operating current when current reduction is intended to operate at the IrDA low power conditions. E.g. for  $V_{CC2} = 3.3$  V a current limiting resistor of  $R_S = 56\ \Omega$  will allow a power minimized operation at IrDA low power conditions.
- Due to this wavelength restriction compared to the IrDA spec of 850 nm to 900 nm the transmitter is able to operate as source for the standard remote control applications with codes as e.g. Phillips RC5/RC6<sup>®</sup> or RECS 80.

### RECOMMENDED SOLDER PROFILES

#### Solder Profile for Sn/Pb Soldering

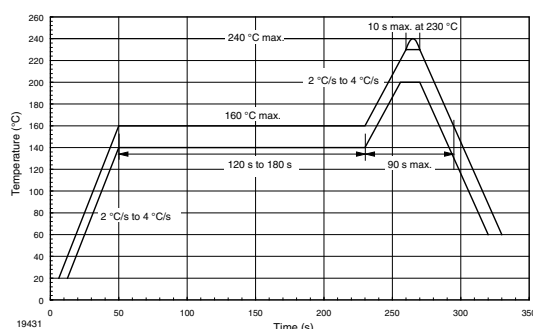


Fig. 1 - Recommended Solder Profile for Sn/Pb Soldering

#### Lead (Pb)-free, Recommended Solder Profile

The TFBS4711 is a lead (Pb)-free transceiver and qualified for lead (Pb)-free processing. For lead (Pb)-free solder paste like  $\text{Sn}_{(3.0 - 4.0)}\text{Ag}_{(0.5 - 0.9)}\text{Cu}$ , there are two standard reflow

profiles: Ramp-Soak-Spike (RSS) and Ramp-To-Spike (RTS). The Ramp-Soak-Spike profile was developed primarily for reflow ovens heated by infrared radiation. With widespread use of forced convection reflow ovens the Ramp-To-Spike profile is used increasingly. Shown in figure 2 is Vishay's recommended profiles for use with the TFBS4711 transceivers. For more details please refer to the application note "SMD Assembly Instructions".

#### Wave Soldering

For TFDUxxxx and TFBSxxxx transceiver devices wave soldering is not recommended.

#### Manual Soldering

Manual soldering is the standard method for lab use. However, for a production process it cannot be recommended because the risk of damage is highly dependent on the experience of the operator. Nevertheless, we added a chapter to the above mentioned application note, describing manual soldering and desoldering.



## TFBS4711

Vishay Semiconductors Serial Infrared Transceiver SIR, 115.2 kbit/s,  
2.4 V to 5.5 V Operation



### Storage

The storage and drying processes for all Vishay transceivers (TFDUxxxx and TFBSxxx) are equivalent to MSL4.

The data for the drying procedure is given on labels on the packing and also in the application note "Taping, Labeling, Storage and Packing".

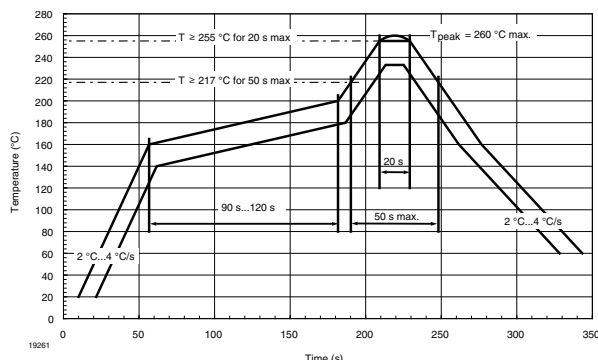


Fig. 2 - Solder Profile, RSS Recommendation

### RECOMMENDED CIRCUIT DIAGRAM

Operated with a clean low impedance power supply the TFBS4711 needs no additional external components. However, depending on the entire system design and board layout, additional components may be required (see figure 1).

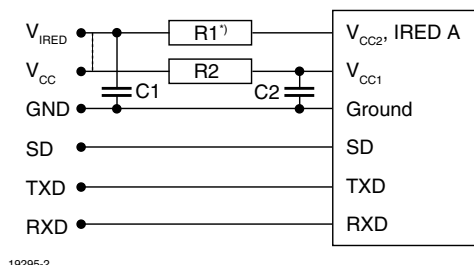


Fig. 3 - Recommended Application Circuit

### Note

\*) R1 is optional when reduced intensity is used

The capacitor C1 is buffering the supply voltage and eliminates the inductance of the power supply line. This one should be a Tantalum or other fast capacitor to guarantee the fast rise time of the IRED current. The resistor R1 is the current limiting resistor, which may be used to reduce the operating current to levels below the specified controlled values for saving battery power.

Vishay's transceivers integrate a sensitive receiver and a built-in power driver. The combination of both needs a careful circuit board layout. The use of thin, long, resistive and inductive wiring should be avoided. The shutdown input must be grounded for normal operation, also when the shutdown function is not used.

### TABLE 1 - RECOMMENDED APPLICATION CIRCUIT COMPONENTS

| COMPONENT | RECOMMENDED VALUE                 | VISHAY PART NUMBER   |
|-----------|-----------------------------------|----------------------|
| C1        | 4.7 $\mu$ F, 16 V                 | 293D 475X9 016B      |
| C2        | 0.1 $\mu$ F, ceramic              | VJ 1206 Y 104 J XXMT |
| R1        | Depends on current to be adjusted |                      |
| R2        | 47 $\Omega$ , 0.125 W             | CRCW-1206-47R0-F-RT1 |

The inputs (TXD, SD) and the output RXD should be directly connected (DC - coupled) to the I/O circuit. The capacitor C2 combined with the resistor R2 is the low pass filter for smoothing the supply voltage. R2, C1 and C2 are optional and dependent on the quality of the supply voltages  $V_{CC1}$  and injected noise. An unstable power supply with dropping voltage during transmission may reduce the sensitivity (and transmission range) of the transceiver.

The placement of these parts is critical. It is strongly recommended to position C2 as close as possible to the transceiver pins.

When extended wiring is used as in bench tests the inductance of the power supply can cause dynamically a voltage drop at  $V_{CC2}$ . Often some power supplies are not able to follow the fast current rise time. In that case another 4.7  $\mu$ F (type, see table under C1) at  $V_{CC2}$  will be helpful.

Under extreme EMI conditions as placing an RF-transmitter antenna on top of the transceiver, we recommend to protect all inputs by a low-pass filter, as a minimum a 12 pF capacitor, especially at the RXD port. The transceiver itself withstands EMI at GSM frequencies above 500 V/m. When interference is observed, the wiring to the inputs picks it up. It is verified by DPI measurements that as long as the interfering RF - voltage is below the logic threshold levels of the inputs and equivalent levels at the outputs no interferences are expected.

One should keep in mind that basic RF - design rules for circuits design should be taken into account. Especially longer signal lines should not be used without termination. See e.g. "The Art of Electronics" Paul Horowitz, Winfield Hill, 1989, Cambridge University Press, ISBN: 0521370957.





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2.4 V to 5.5 V Operation

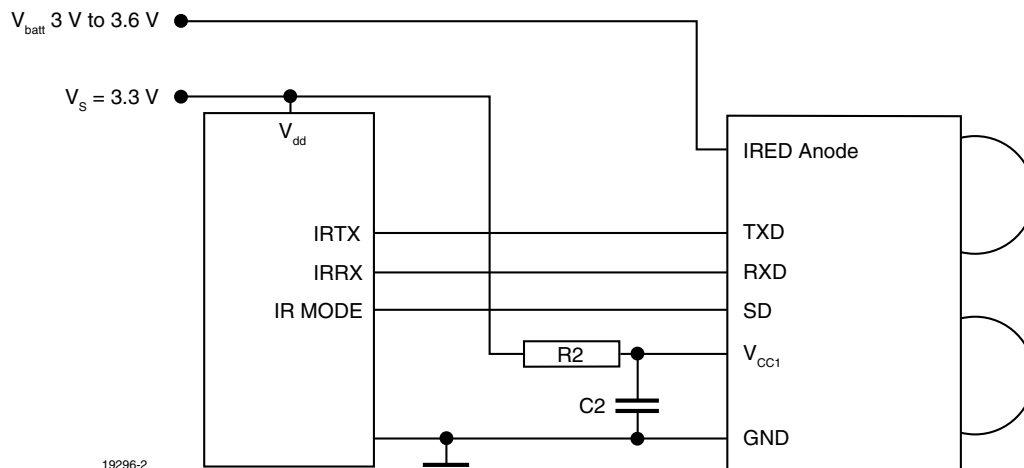


Fig. 4 - Typical Application Circuit

Figure 4 shows an example of a typical application for to work with a separate supply voltage  $V_S$  and using the transceiver with the IRED anode connected to the unregulated battery  $V_{batt}$ . This method reduces the peak load of the regulated power supply and saves therefore costs. Alternatively all supplies can also be tied to only one voltage source. R1 and C1 are not used in this case and are depending on the circuit design in most cases not necessary.

### I/O AND SOFTWARE

In the description, already different I/Os are mentioned. Different combinations are tested and the function verified with the special drivers available from the I/O suppliers. In special cases refer to the I/O manual, the Vishay application notes, or contact directly Vishay Sales, Marketing or Application.

For operating at RS232 ports the ENDECS TOIM4232 or TOIM5232 is recommended.

#### Note

TFBS4711 echoes the TXD signal at the RXD output during transmission. For communication this signal is to be correctly ignored by the controller or the software. The echo signal is implemented for test purposes in mass production.

### CURRENT DERATING DIAGRAM

Figure 5 shows the maximum operating temperature when the device is operated without external current limiting resistor.

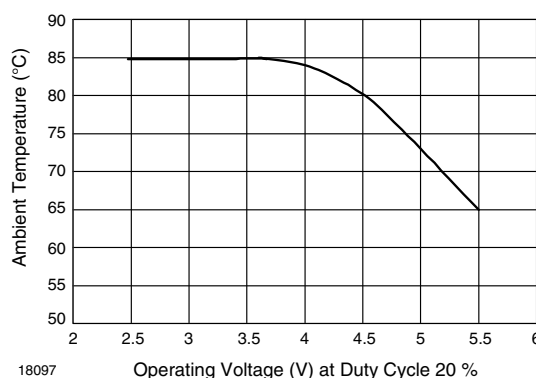


Fig. 5 - Current Derating Diagram



## TFBS4711

Vishay Semiconductors Serial Infrared Transceiver SIR, 115.2 kbit/s,  
2.4 V to 5.5 V Operation



**TABLE 2 - TRUTH TABLE**

| INPUTS         |                       |  | OUTPUTS  |                | REMARK   |
|----------------|-----------------------|--|--|----------------|--|
| SD             | TXD                   | OPTICAL INPUT IRRADIANCE<br>mW/m <sup>2</sup>                                  | RXD  | TRANSMITTER    | OPERATION  |
| High<br>> 1 ms | x                     | x  | Weakly pulled<br>(500 $\Omega$ ) to V <sub>CC1</sub> | 0              | Shutdown   |
| Low            | High                  | x  | Low (active)   | I <sub>e</sub> | Transmitting   |
| Low            | High<br>> 100 $\mu$ s | x  | High inactive  | 0              | Protection is active   |
| Low            | Low                   | < 4  | High inactive  | 0              | Ignoring low signals below the<br>IrDA defined threshold for noise<br>immunity |
| Low            | Low                   | > min. detection threshold irradiance<br>< max. detection threshold irradiance | Low (active)   | 0              | Response to an IrDA compliant<br>optical input signal                          |
| Low            | Low                   | > min. detection threshold irradiance  | Undefined  | 0              | Overload conditions can cause<br>unexpected outputs                            |

### PACKAGE DIMENSIONS in millimeters

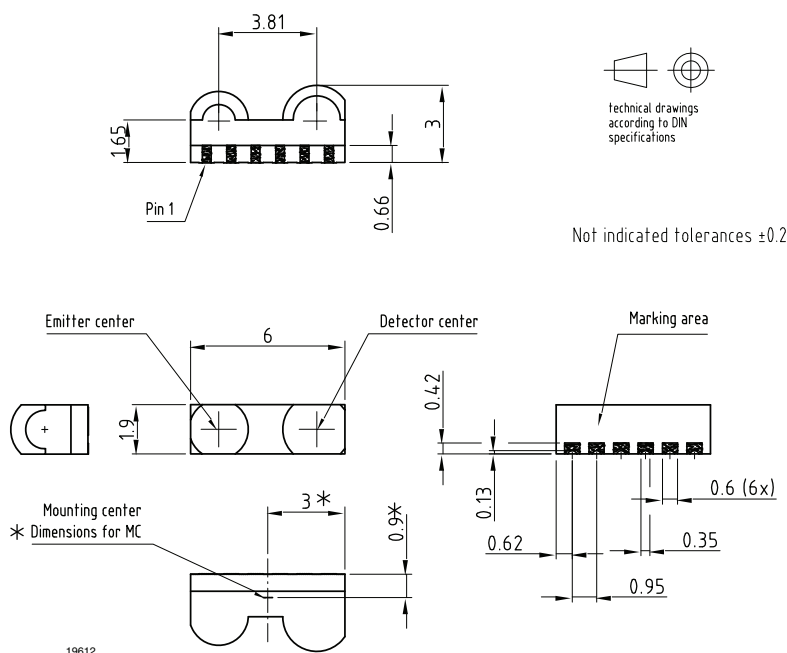


Fig. 6 - Package Drawing of TFBS4711, Tolerance of Height is + 0.1 mm, - 0.2 mm, other Tolerances  $\pm$  0.2 mm

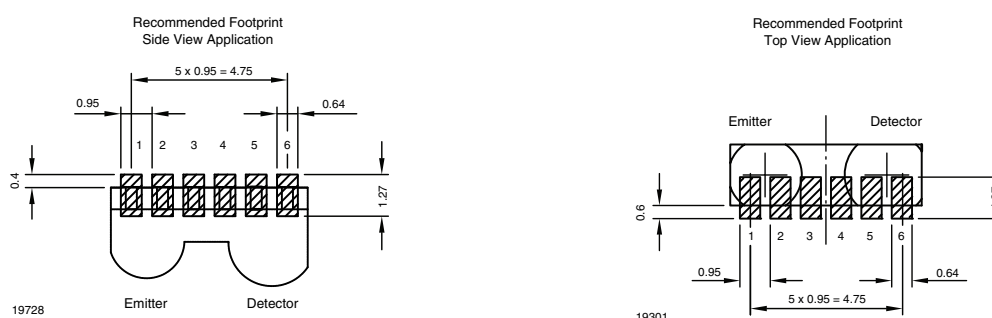


Fig. 7 - Soldering Footprints



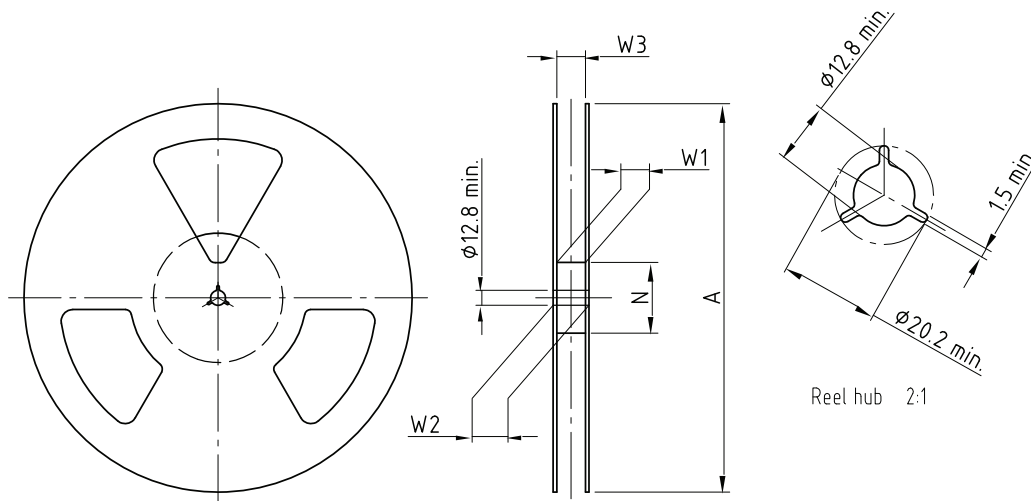


## TFBS4711

Serial Infrared Transceiver SIR, 115.2 kbit/s,  
2.4 V to 5.5 V Operation

Vishay Semiconductors

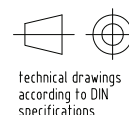
### REEL DIMENSIONS in millimeters



Drawing-No.: 9.800-5090.01-4  
Issue: 1; 29.11.05  
14017

Form of the leave open  
of the wheel is supplier specific.

Dimension acc. to IEC EN 60 286-3



| TAPE WIDTH<br>(mm) | A MAX.<br>(mm) | N<br>(mm) | W <sub>1</sub> MIN.<br>(mm) | W <sub>2</sub> MAX.<br>(mm) | W <sub>3</sub> MIN.<br>(mm) | W <sub>3</sub> MAX.<br>(mm) |
|--------------------|----------------|-----------|-----------------------------|-----------------------------|-----------------------------|-----------------------------|
| 16                 | 330            | 50        | 16.4                        | 22.4                        | 15.9                        | 19.4                        |

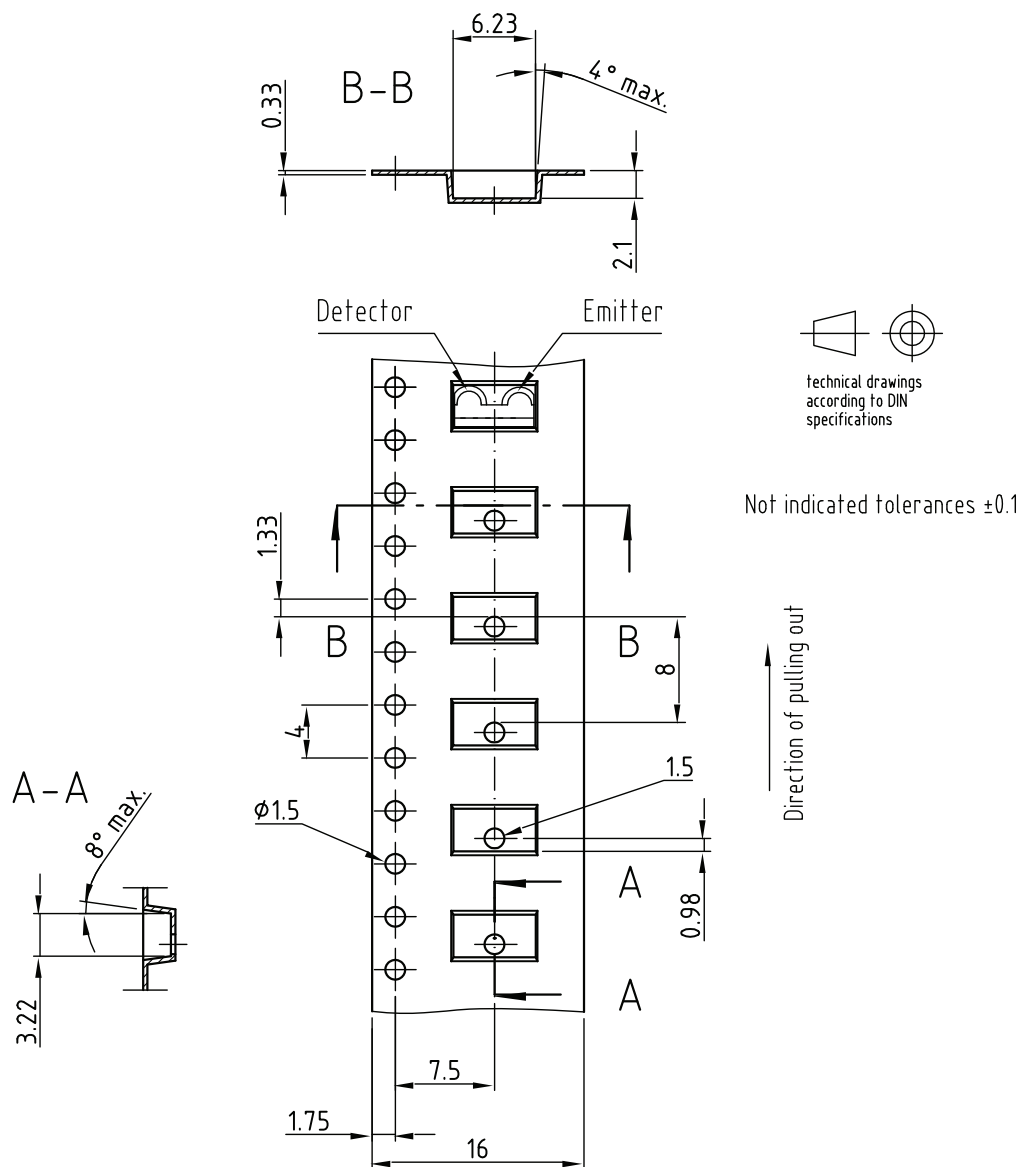


## TFBS4711

Vishay Semiconductors Serial Infrared Transceiver SIR, 115.2 kbit/s,  
2.4 V to 5.5 V Operation



### TAPE DIMENSIONS FOR TR in millimeters



Drawing-No.: 9.700-5294.01-4

Issue: 1; 08.12.04

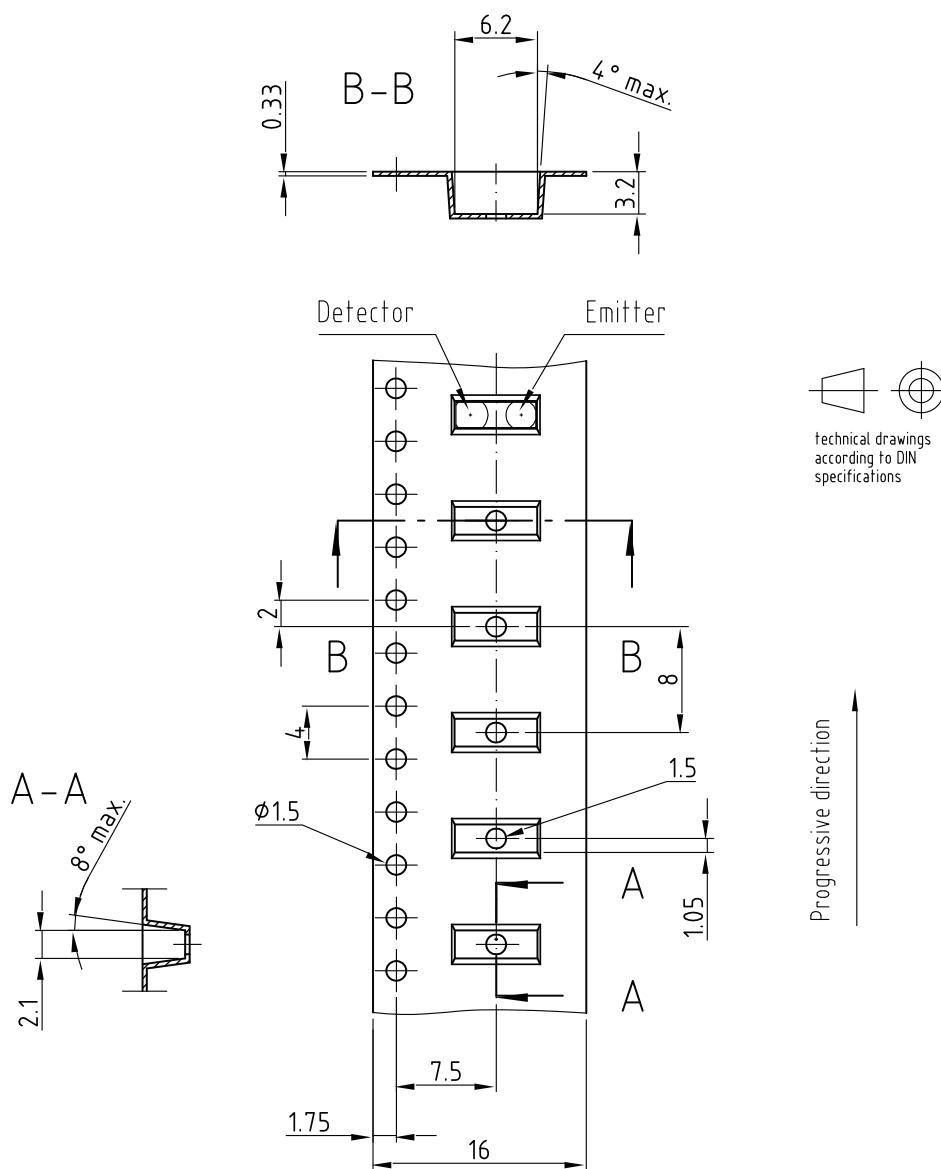
19613



**TFBS4711**Serial Infrared Transceiver SIR, 115.2 kbit/s,  
2.4 V to 5.5 V Operation

Vishay Semiconductors

### TAPE DIMENSIONS FOR TT in millimeters



Drawing-No.: 9.700-5295.01-4  
Issue: 1; 08.12.04  
20416





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